

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

2 Priority Application Serial No. 08/710,353
3 Priority Filing Date 09/17/96
4 Inventor Pai-Hung Pan
5 Assignee Micron Technology, Inc.
6 Priority Group Art Unit 1107
7 Priority Examiner B. Mee
8 Attorney's Docket No. MI22-898
9 Title: Semiconductor Processing Methods of Forming a Conductive Gate and Line

PRELIMINARY AMENDMENT

10 To: Box PATENT APPLICATION
11 Assistant Commissioner for Patents
12 Washington, D.C. 20231

13 From: Lance R. Sadler (Tel. 509-624-4276; Fax 509-838-3424)
14 Wells, St. John, Roberts, Gregory & Matkin P.S.
15 601 W. First Avenue, Suite 1300
16 Spokane, WA 99201-3817

17 Sir:

18 Applicant preliminarily amends as follows:

AMENDMENTS

In the Specification

19 At p. 1 before the "Technical Field" section, please insert the
20 following:

--RELATED PATENT DATA

21 This patent resulted from a continuation application of U.S. Patent
22 Application Serial No. 08/710,353, filed September 17, 1996, entitled
23 "Semiconductor Processing Methods of Forming a Conductive Gate and
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